

1024-BIT BIPOLAR PROGRAMMABLE ROM (256X4 PROM) **82527**

JULY 1975

DIGITAL 8000 SERIES TTL/MEMORY

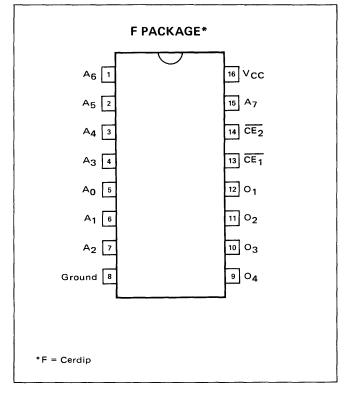
DESCRIPTION

The 82S27 is a Bipolar 1024-Bit Read Only Memory, organized as 256 words by 4 bits per word. It is Field-Programmable, which means that custom patterns are immediately available by following the fusing procedure given in this data sheet. The standard 82S27 is supplied with all outputs at logical "O". Outputs are programmed to a logic "1" level at any specified address by fusing a Ni-Cr link matrix.

The 82S27 is fully TTL compatible, and includes on-chip decoding, two chip enable inputs, and open collector outputs for ease of memory expansion.

The 82S27 is available in the commercial temperature range. For the commercial temperature range ($0^{\circ}C$ to +75 $^{\circ}C$) specify N82S27, F.

PIN CONFIGURATION



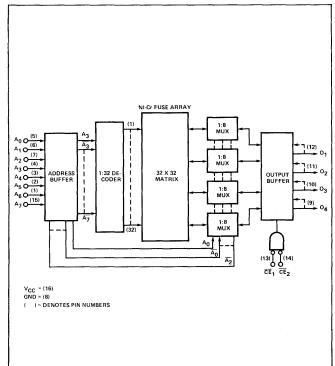
FEATURES

- ORGANIZATION 256 X 4
- ADDRESS ACCESS TIME 40ns, MAXIMUM
- POWER DISSIPATION 0.6mW/BIT, TYPICAL
- INPUT LOADING 1.6mA, MAXIMUM
- TWO CHIP ENABLE INPUTS
- ON-CHIP ADDRESS DECODING
- OPEN COLLECTOR OUTPUTS
- NO SEPARATE "FUSING" PINS
- UNPROGRAMMED OUTPUTS ARE "0" LEVEL
- 16-PIN CERAMIC DIP

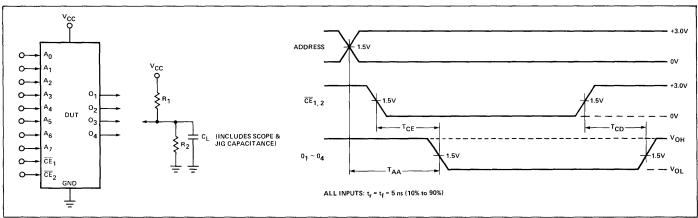
APPLICATIONS

PROTOTYPING/VOLUME PRODUCTION SEQUENTIAL CONTROLLERS MICROPROGRAMMING HARDWIRED ALGORITHMS CONTROL STORE RANDOM LOGIC CODE CONVERSION

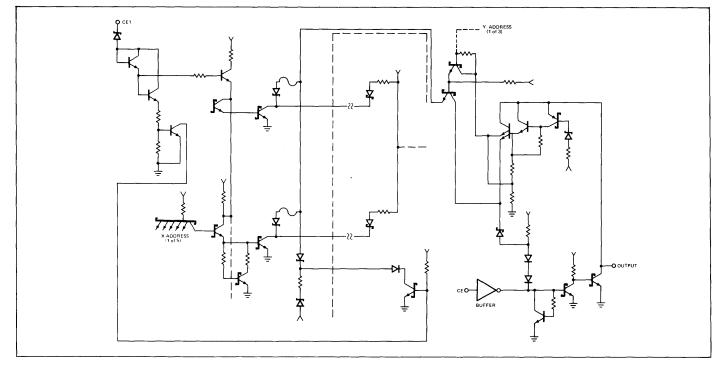
BLOCK DIAGRAM



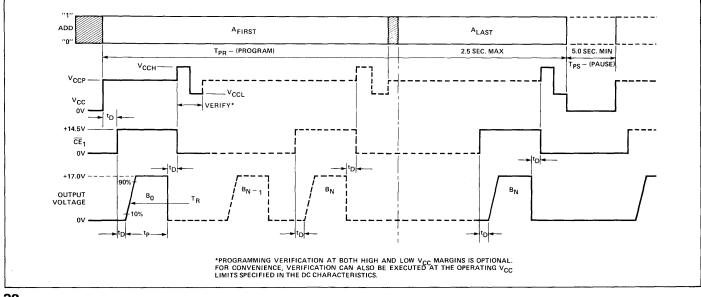
AC TEST FIGURE AND WAVEFORM



TYPICAL FUSING PATH



TYPICAL PROGRAMMING SEQUENCE



ABSOLUTE MAXIMUM RATINGS

	PARAMETER	RATING	UNIT	
V _{CC}	Power Supply Voltage	+7	Vdc	
V _{IN}	Input Voltage	+5.5	Vdc	
V _{OH}	High Level Output Voltage	+5.5	Vdc	
TA	Operating Temperature Range	0 [°] to +75 [°]	°C	
T _{stg}	Storage Temperature Range	-65° to $+150^{\circ}$	°C	

ELECTRICAL CHARACTERISTICS $0^{\circ}C \leq T_{A} \leq +75^{\circ}C$, $4.75V \leq V_{CC} \leq 5.25V$

PARAMETER		TEAT CONDITIONS	LIMITS			
		TEST CONDITIONS ¹	MIN	TYP ²	MAX	UNIT
VOL	"0" Output Voltage	I _{OUT} = 32mA		0.45	0.50	v
IOLK	Output Leakage Current	$\overline{CE_1}$ or $\overline{CE_2}$ = "1", V_{OUT} = 5.5V			100	μA
Чн	"1" Input Current	V _{IN} = 2.4V V _{IN} = 5.5V			40 1	μA mA
LIL I	"0" Input Current	V _{IN} = 0.50V			-1.6	mA
VIL	"0" Level Input Voltage				.80	v
V _{IH}	"1" Level Input Voltage		2.0			v
Icc	V _{CC} Supply Current			120	140	mA
V _{IC}	Input Clamp Voltage	$I_{\rm IN} = -12 {\rm mA}$		-1.0	-1.5	v
CIN	Input Capacitance	V _{IN} = 2.0V, V _{CC} = 5.0V		5		pF
С _{ОИТ}	Output Capacitance	$\frac{V_{OUT}}{CE_1} = 2.0V, V_{CC} = 5.0V,$ $\frac{V_{CE_1}}{CE_2} = "1"$		8		pF

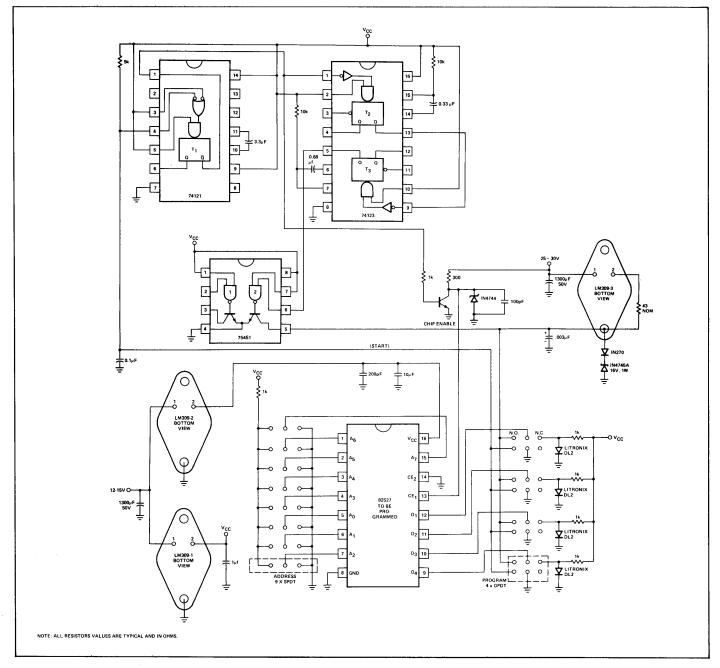
SWITCHING CHARACTERISTICS $0^{\circ}C \leq T_{A} \leq +75^{\circ}C$, $4.75V \leq V_{CC} \leq 5.25V$

	TEST CONDITIONS	LIMITS			
PARAMETER		MIN	TYP ²	MAX	UNIT
Propagation Delay					
T _{AA} Address to Output	$C_L = 30pF$		30	40	ns
T _{CD} Chip Disable to Output	$R_1 = 270\Omega$		15	20	ns
T _{CE} Chip Enable to Output	$R_2 = 600\Omega$		15	20	ns

NOTES:

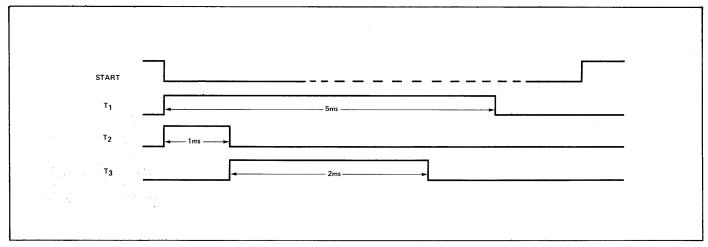
SIGNETICS 1024-BIT BIPOLAR PROGRAMMABLE ROM (256 X 4 PROM) = 82S27

MANUAL PROGRAMMER



TIMING SEQUENCE

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		TEST CONDITIONS		LIMITS		
	PARAMETER		MIN	ТҮР	МАХ	UNIT
Power S	Supply Voltage					
V _{CCP} ¹	To Program	I _{CCP} = 300 ± 50mA (Transient or steady state)	5.0		5.25	V
V _{CCH}	Upper Verify Limit		5.0	5.25	5.5	V
V _{CCL}	Lower Verify Limit		4.5	4.75	5.0	v
V _S ³	Verify Threshold		0.9	1.0	1.1	v
ICCP	Programming Supply Current	$V_{CCP} = +5.0 \pm 0.25V$	250	300	350	mA
Input V	oltage					
VIH	Logical ''1'' (Except $\overline{CE_1}$)		3.0		5.0	v
V _{IN}	Program Level (\overline{CE}_1 Only)		14.0	14.5	15.0	v
VIL	Logical "0"		0	0.4	0.5	v
Input C	urrent					
LIH	Logical "1"	V _{IH} = +3.0V			100	μΑ
۱ _{۱۲}	Logical ''0''	V _{IL} = +0.5V			-1.6	mA
I _{IN}	Program Level (CE ₁ Only)	V _{IN} = +15.0V			15	mA
V _{OUT} ²	Output Programming Voltage	$I_{OUT} = 115 \pm 10 \text{mA}$ (Transient or steady state)	16.5	17.0	17.5	V
IOUT	Output Programming Current	V _{OUT} = +17.0 ± 0.5V	105	115	125	mA
T _R ⁵	Output Pulse Rise Time		0.2		0.5	μs
tp	Programming Pulse Width		1		2	ms
t _D	Pulse Sequence Delay		10			μs
TPR	Programming Time	V _{CC} = V _{CCP}			2.5	sec
T _{PS}	Programming Pause	V _{CC} = 0V	5			sec
T _{PR} ⁴ T _{PB} +T _F	– Programming Duty Cycle				33	%

PROGRAMMING SPECIFICATIONS (Testing of these limits may cause programming of device.) $T_A = +25^{\circ}C$

PROGRAMMING PROCEDURE

The 82S27 is shipped with all bits at logical "0" (low). To write logical "1", proceed as follows:

SET-UP

- a. Apply GND to pin 12.
- b. Terminate all device outputs with a 10k Ω resistor to VCC.
- c. Set CE₂ to logic "0".

PROGRAM-VERIFY SEQUENCE

- Step 1 Raise V_{CC} to V_{CCP}, and address the word to be programmed by applying TTL "1" and "0" logic levels to the device address inputs.
- Step 2 After 10 μ s delay, apply to \overline{CE}_1 (pin 13) a voltage source of 14.5 ± 0.5V, with 15mA sourcing current capability.

NOTES:

- 1. Bypass V_{CC} to GND with a 0.01 μ F capacitor to reduce voltage spikes.
- 2. Care should be taken to insure the 17 ± 0.5V output voltage is maintained during the entire fusing cycle. The recommended supply is a constant current source clamped at the specified voltage limit.
- 3. V_S is the sensing threshold of the PROM output voltage for a programmed bit. It normally constitutes the reference voltage applied to a comparator circuit to verify a successful fusing attempt.
- Continuous fusing for an unlimited time is also allowed, provided that a 33% duty cycle is maintained. This may be accomplished by following each Program Verify cycle with a Rest period (V_{CC} = 0V) of 4ms.
- 5. Measured with a 1k dummy load connected across the fusing source.

- Step 3 After 10 μ s delay, apply a voltage source of +17.0 \pm 0.5V to the output to be programmed. The source must have a current limit of 115mA. Program one output at the time.
- Step 4 After $10\mu s$ delay, remove +17.0V supply from programmed output.
- Step 5 <u>To</u> verify programming, after 10 μ s delay, return CE₁ to 0V. Raise V_{CC} to V_{CCH} = +5.25 ± .25V. The programmed output should remain in the "1" state. Again, lower V_{CC} to V_{CCL} = +4.75 ± .25V, and verify that the programmed output remains in the "1" state.
- Step 6 Raise V_{CC} to V_{CCP}, and repeat steps 2 through 5 to program other bits at the same address.
- Step 7 Repeat steps 1 through 6 to program all other address locations.